



1.8V 20Gbps DP 2.1 Linear ReDriver with AUX Listener & I2C Control

Description

The DIODES PI2DPX2063 is a 20Gbps DP 2.1 linear ReDriver™ in a 4-to-4 configuration operated by a 1.8V power supply. The device supports UHBR20 (DP2.1 20Gbps), UHBR13.5 (DP2.1 13.5Gbps), UHBR10 (DP2.1 10Gbps), HBR3 (DP1.4 8.1Gbps), HBR2 (DP1.2 5.4Gbps), HBR (DP1.1 2.7Gbps) and RBR(DP1.0 1.62Gbps) under various DisplayPort speeds. With the on-chip AUX channel listener, the device can automatically monitor the system operation status to enter D3 power saving mode.

The non-blocking linear ReDriver design ensures that the differential signals conveying pre-shoot and de-emphasis equalization waveforms from the transmitter side to the receiver side help optimize the overall channel link adjustment conducted by the system transmitter and receiver that has been equipped with DFE. The CTLE equalizers are implemented at the inputs of the ReDriver to compensate the channel loss and reduce the ISI jitters. The programmable flat gain adjustments support the eye diagram opening.

The CTLE EQ gains and flat gains are individually programmable on each channel for flexible tuning via I2C register settings.

Application(s)

- Laptop, Desktop and AIO PCs
- Workstation and Server
- · Docking Station
- Display Monitor
- Gaming Console
- Active Cable

Features

- 4-to-4 Linear ReDriver Channel Configuration with CTLE Gain Compensation Up to 16.2dB @20Gbps
- Supports 4-Lane DP2.1 (UHBR20/UHBR13.5/UHBR10)/ HDBR3/HBR2/RBR
- Ultra Low Latency (<300ps) for Better Interoperability and Data Throughput
- Individual Controls on CTLE Gain (6 to 16.2dB), Flat Gain (-4 to +2dB)
- Integrated AUX Channel Listener for D3 Power Saving Mode
- I2C Slave Support with Speed Up to 1MHz
- Low Active Current Consumption
- 4-Lane DP: 160mA (Typical)
- Support DisplayPort Dual Mode
- Single Power Supply: 1.8V +/-5%
- Industrial Temperature Support: -40°C to +85°C
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.
 - https://www.diodes.com/quality/product-definitions/
- Packaging (Pb-free & Green):
 - Tiny 32-pin, WLGA, 2.85 x 4.5 mm (0.4 mm pitch) (FLA)

Ordering Information

Ordering Number	Package Code	Description
PI2DPX2063FLAEX	FLA	32-Pin, W-LGA4528-32

Notes:

- E = Pb-free and Green
- X suffix = Tape/Reel

Notes

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



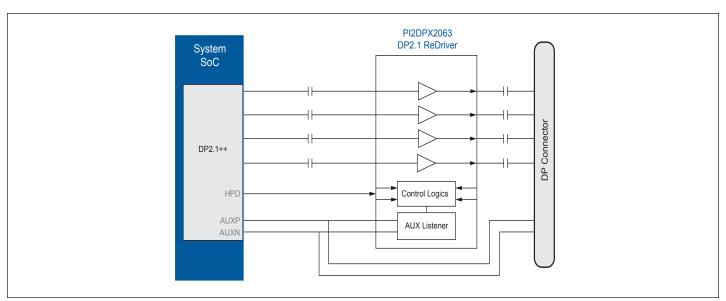


Revision History

Date	Revision	Description	
August 2021	1	Preliminary Datasheet Release	
July 2022	2	Updated Absolute Maximum Ratings Updated CTLE Equalization Gain Updated Feature Updated Configuration Table	
		Updated Diodes Format Added Recommended Land Pattern	
June 2024	3	Added Control Pin Specifications Updated Feature Updated AC/DC Characteristics Updated I2C Electrical Specification and Timing Updated Application Schematics Updated Pin Configuration and Description	
		Updated Pin Configuration and Description Updated I2C Register Definitions Updated Power Consumption Updated Table 2 I/O Termination Resistance under Different Conditions	





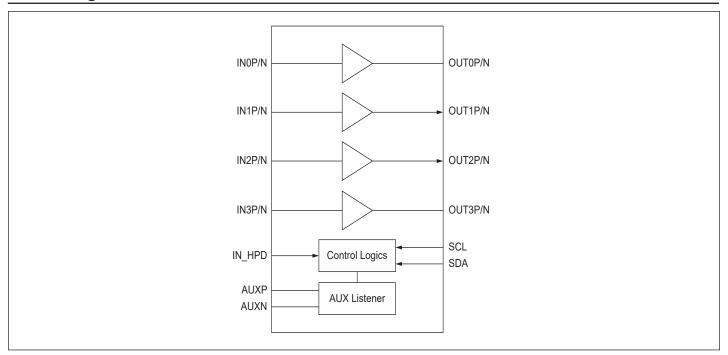


PI2DPX2063 in DP2.1 PC Motherboard Application





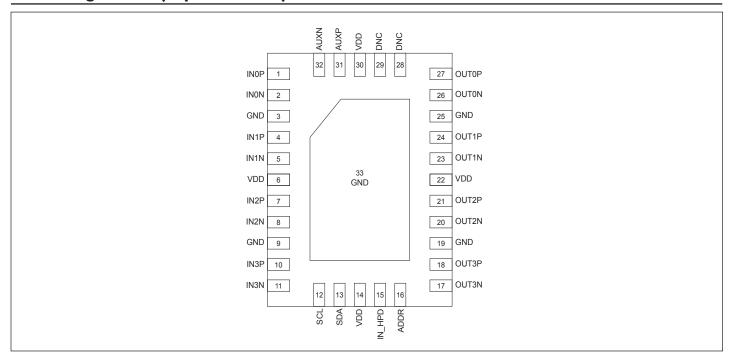
Block Diagram







Pin Configuration (Top-Side View)



Pin Description

Pin #	Pin Name	Type	Description
Power and GND			
6, 14, 22, 30	VDD	Power	1.8V power supply, ±5%
3, 9, 19, 25, 33	GND	Ground	Supply ground
Control Pins			
12	SCL	I	SCL is I2C control bus clock. Open drain structure.
13	SDA	I/O	SDA is I2C control bus data. Open drain structure.
			Hot plug detection from Sink.
15	IN_HPD	I	With I2C (IN_HPD_HIZ) selectable internal 300k Ω pull-down resistor.
			IN_HPD_HIZ='0', 300k Ω pull-down. Otherwise, the pin is HiZ
16	ADDR	T	The I2C address select. 4-level input pin. With internal $100K\Omega$ pull-up and $200K\Omega$ pull-down resistors.
			External Pulldown resistor value is $68K\Omega$.
High Speed I/O P	ins		
18,	OUT3P,		
17	OUT3N		Channel CML output terminals.
27,	OUT0P,	О	With selectable output termination between 50Ω to VDD, $6k\Omega$ to internal VbiasTx or Hi-Z
26	OUT0N		





Pin #	Pin Name	Туре	Description
21,	OUT2P,		
20	OUT2N		Channel CML output terminals.
24,	OUT1P,	О	With selectable output termination between 50Ω to VDD, $6K\Omega$ to internal VbiasTx or Hi-Z.
23	OUT1N		
1,	INOP,		
2	IN0N	_	Channel CML input terminals.
10,	IN3P,	I	With selectable input termination between 50Ω to internal VbiasRx, or $78K\Omega$ to internal VbiasRx.
11	IN3N		The first of the f
4,	IN1P,		
5	IN1N	_	Channel CML input terminals.
7,	IN2P,	I	With selectable input termination between 50Ω to internal VbiasRx, or $78K\Omega$ to internal VbiasRx.
8	IN2N		internal votables.
Side Band Si	gnal Pins	,	•
29, 28	DNC		Do Not connect
31, 32	AUXP, AUXN	I/O	DisplayPort AUX CH differential signal connections





Operation Mode

Table 1. Configuration Table

OP_MODE<3:0>	IN0	IN1	IN2	IN3	AUXP	AUXN	Mode
0000-0001	-	-	-	-	-	_	Reserved
0010	OUT0	OUT1	OUT2	OUT3			4-lane DP + AUX
0010	(DP0)	(DP1)	(DP2)	(DP3)	_	_	4-latte DF + AUA
0011	OUT0 (DP3)	OUT1 (DP2)	OUT2 (DP1)	OUT3 (DP0)	_	_	4-lane DP + AUX (flipped)
<0100> ~ <1111>	_	_	_	_	_	_	Reserved

Notes: 1) <0010> default at power on.

Table 2. I/O Termination Resistance under Different Conditions

Symbol	Parameter	Resistance	Units
RX Terminal			
R _{in-pd}	Input res at IN_HPD = 0	78k to GND	Ω
R _{in-Active}	Input res at active mode condition	50 to VbiasRx1	Ω
R _{in-DP-standby}	Input res in DP standby mode	78k to GND	Ω
R _{in-DP-active}	Input res in DP active mode	50 to VbiasRx1	Ω
R _{in-DP-D3}	Input res in DP D3 mode	78k to GND	Ω
TX Terminal			
R _{out-pd}	Output res at IN_HPD = 0	78k to GND	Ω
R _{out-Active}	Output res at active mode condition	50 to VDD	Ω
R _{out-DP-standby}	Output res in DP standby mode	78k to GND	Ω
R _{out-DP-active}	Output res in DP active mode	50 to VDD	Ω
R _{out-DP-D3}	Output res in DP D3 mode	78k to GND	Ω

DisplayPort Mode

By default, all channels will go to active mode if HPD bit = 1. The ON/OFF of each DP channel is controlled by the Aux lane count.

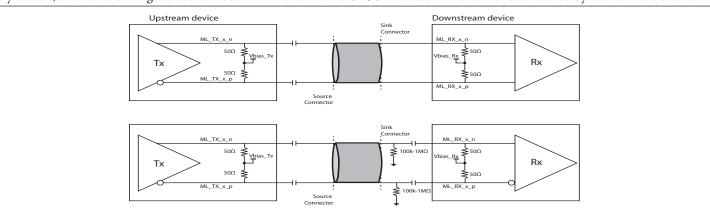


Figure 1. DisplayPort Main Link Connection Diagram





DisplayPort Main Link

The electrical sub-block of a DP Main-Link consists of up to four differential pairs. The DP TX drives doubly terminated, AC-coupled differential pairs in a manner compliant with the Main-Link Transmitter electrical specification.

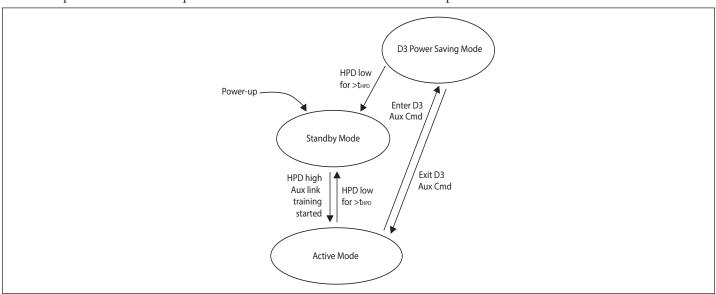


Figure 2. DisplayPort Operation Modes

Table 3. Description of DP Operating Mode

PM_State	Mode	Description
1	Standby Mode	Low power consumption (AUX listener is OFF); Main Link outputs are disabled
2	Active Mode	Data transfer (normal operation); AUX listener is active. The AUX listener is actively monitoring for Link Training unless it is disabled through I2C interface. After power-up and in active mode, all Main Link outputs are enabled. AUX Link Training is necessary to overwrite the DPCD registers to enable/disable Main Link outputs.
3	D3 Power Saving Mode	Low power consumption(AUX listener is active); Main Link outputs are disabled





CTLE Equalization, Flat Gain and Chip Enable Controls

Table 4. CTLE Equalization Gain (Typical Values at FG = 0dB)

I2C Reg	gister Setting E	EQ<2:0>	Equalizer Setting (dB)				
EQ<2>	EQ<1>	EQ<0>	@1.35GHz	@2.5GHz	@4GHz	@5GHz	@10GHz
0	0	0	-0.1 (Default)	0.1 (Default)	0.7 (Default)	1.3 (Default)	6.0 (Default)
0	0	1	0.0	0.6	1.6	2.5	8.5
0	1	0	0.2	1.3	2.8	4.1	10.8
0	1	1	0.6	2.2	4.3	5.8	12.7
1	0	0	1.1	3.5	6.0	7.7	14.2
1	0	1	1.7	4.8	7.6	9.3	15.2
1	1	0	2.6	6.3	9.2	10.8	15.8
1	1	1	3.5	7.5	10.4	11.8	16.2

Note: F: Floating, R: External resistor to ground.

Table 5. Flat Gain Setting (FG)

I2C Regist	er FG[1:0]	Flat Gain Setting
0	0	-4 dB
0	1	-2 dB
1	0	+0 dB (Default)
1	1	+2 dB





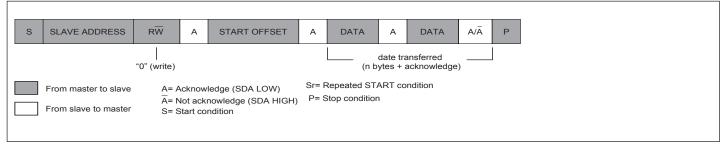
Detailed Programming Registers

I2C Slave Address Selections

			I2C Slav	ve Address Ass	ignment		
A6	A5	A4	A3	A2	A1	A0	ADDR (Pin 16)
1	0	1	0	0	0	0	L
1	0	1	0	0	0	1	R
1	0	1	0	0	1	0	F
1	0	1	0	0	1	1	Н



Indexed Read



Indexed Write

I2C Register Definitions

BYTE 0 (Revision and Vendor ID Register)

21120 (110	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	1001 120 11081011)	
Bit	Туре	Power-up Condition	Comment
7	RO	0	
6	RO	0	Desiring ID 0000
5	RO	0	Revision ID = 0000
4	RO	0	
3	RO	0	
2	RO	0	D: 1 ID 0011
1	RO	1	Diodes ID = 0011
0	RO	1	





7 RO 0 6 RO 0 5 RO 0 4 RO 1 3 RO 0 2 RO 1 1 RO 0 0 RO 0	Bit	Type	Power-up Condition	Comment	
5 RO 0 4 RO 1 3 RO 0 2 RO 1 1 RO 0 Device Type = Active Mux Device Type = Active Mux Device Type = Active Mux	7	RO	0		
5 RO 0 4 RO 1 3 RO 0 2 RO 1 1 RO Device ID	6	RO	0		
3 RO 0 2 RO 1 1 RO 0	5	RO	0	Device Type = Active Mux	
2 RO 1 1 RO 0 Device ID	4	RO	1		
1 RO 0 Device ID	3	RO	0		
1 RO 0	2	RO	1		
0 RO 0	1	RO	0	Device ID	

` '			
Bit	Type	Power-up Condition	Comment
7	RO	0	
6	RO	0	
5	RO	1	
4	RO	0	IAC Desister Posts County 22 bests
3	RO	0	I2C Register Byte Count = 32 bytes
2	RO	0	
1	RO	0	
0	RO	0	

BYTE 3 (Channel Assignment of RXDET_EN#)

`		_ <i> </i>	
Bit	Type	Power-up Condition	Comment
7	R/W	0	
6	R/W	0	Operation Mode Setting
5	R/W	1	Refer to Table Configuration Table
4	R/W	0	
3	R/W	0	Reserved
2	R/W	0	Reserved
1	R/W	1	Reserved
0	R/W	1	Reserved





TTE 4 (Override the Power Down Control)			
Bit	Type	Power-up Condition	Comment
7	R/W	0	CON3 power down override 0 – Do not force the CON3 to power down state 1 – Force the CON3 to power down state
6	R/W	0	CON2 power down override 0 – Do not force the CON2 to power down state 1 – Force the CON2 to power down state
5	R/W	0	CON1 power down override 0 – Do not force the CON1 to power down state 1 – Force the CON1 to power down state
4	R/W	0	CON0 power down override 0 – Do not force the CON0 to power down state 1 – Force the CON0 to power down state
3	R/W	0	
2	R/W	0	n 1
1	R/W	0	Reserved
0	R/W	0	

BYTE 5 (Equalization and Flat Gain Setting of CON0)

` 1	L		•
Bit	Type	Power-up Condition	Comment
7	R/W	0	Reserved
6	R/W	0	CON0_EQ<2> Equalizer setting
5	R/W	0	CON0_EQ<1> Equalizer setting
4	R/W	0	CON0_EQ<0> Equalizer setting
3	R/W	1	CON0_FG<1> Flat gain setting
2	R/W	0	CON0_FG<0> Flat gain setting
1	R/W	0	Reserved
0	R/W	0	Reserved





BYTE 6 (Eq	ualization and	d Flat Gain Setting of CO	N1)
Bit	Type	Power-up Condition	Comment
7	R/W	0	Reserved
6	R/W	0	CON1_EQ<2> Equalizer setting
5	R/W	0	CON1_EQ<1> Equalizer setting
4	R/W	0	CON1_EQ<0> Equalizer setting
3	R/W	1	CON1_FG<1> Flat gain setting
2	R/W	0	CON1_FG<0> Flat gain setting
1	R/W	0	Reserved
0	R/W	0	Reserved
BYTE 7 (Eq	ualization and	d Flat Gain Setting of CO	N2)
Bit	Type	Power-up Condition	Comment
7	R/W	0	Reserved
6	R/W	0	CON2_EQ<2> Equalizer setting
5	R/W	0	CON2_EQ<1> Equalizer setting
4	R/W	0	CON2_EQ<0> Equalizer setting
3	R/W	1	CON2_FG<1> Flat gain setting
2	R/W	0	CON2_FG<0> Flat gain setting
1	R/W	0	Reserved
0	R/W	0	Reserved
BYTE 8 (Eq	ualization and	d Flat Gain Setting of CO	DN3)
Bit	Type	Power-up Condition	Comment
7	R/W	0	Reserved
6	R/W	0	CON3_EQ<2> Equalizer setting
5	R/W	0	CON3_EQ<1> Equalizer setting
4	R/W	0	CON3_EQ<0> Equalizer setting
3	R/W	1	CON3_FG<1> Flat gain setting
2	R/W	0	CON3_FG<0> Flat gain setting
1	R/W	0	Reserved
	D /IA7	0	n 1

0

R/W

0

Reserved





Bit	Type	Power-up Condition	Comment
7	R/W	0	Reserved
6	R/W	1	Reserved
5	R/W	1	Reserved
4	R/W	0	Reserved
3	R/W	0	Reserved
2	R/W	0	Reserved
1	R/W	0	AUX flip for AUXSBU1/2 and AUXP/N 0 – Flip is disabled 1 – Flip is enabled
0	R/W	0	DP FLIP DP flip for ALL CONx channels 0 – DP Flip is Disabled 1 – DP Flip is Enabled
BYTE 10 (R	Reserved)		
Bit	Type	Power-up Condition	Comment
7	R/W	1	
6	R/W	1	
5	R/W	1	
4	R/W	1	
3	R/W	1	Reserved
2	R/W	1	
1	R/W	0	
0	R/W	0	
3YTE 11 (R	Reserved)		
Bit	Type	Power-up Condition	Comment
7	R/W	1	
6	R/W	1	
5	R/W	1	
4	R/W	1	
3	R/W	1	Reserved
2	R/W	1	
1	R/W	0	





BYTE 12 (R	BYTE 12 (Reserved)			
Bit	Туре	Power-up Condition	Comment	
7	R/W	0		
6	R/W	0		
5	R/W	1		
4	R/W	1		
3	R/W	0	Reserved	
2	R/W	0		
1	R/W	0		
0	R/W	1		

BYTE 13 - BYTE 15 (Reserved)

BYTE 16 (AUX and HPD Monitor)

Bit	Type	Power-up Condition	Comment
7	RO	N/A	Reserved
6	RO	N/A	Reserved
5	RO	N/A	AUX_IDLE_DET# Detect the AUX activities "0" – Idle "1" – has activities
4	RO	N/A	DP_HPD The condition of IN_HPD 0 - De-asserted 1 - Asserted Notes: When DP_HPD_PIN_EN#=1, then, this value is 1 always.
3	RO	N/A	AP0_RX_SEL "0" AP0 is TX terminal. "1" AP0 is RX terminal
2	RO	N/A	AP3_RX_SEL "0" AP3 is TX terminal. "1" AP3 is RX terminal
1	RO	N/A	CON0_RX_SEL "0" CON0 is TX terminal. "1" CON0 is RX terminal
0	RO	N/A	CON3_RX_SEL "0" CON3 is TX terminal. "1" CON3 is RX terminal





BYTE 17 (R	BYTE 17 (Reserved)			
Bit	Type	Power-up Condition	Comment	
7	RO	0		
6	RO	0		
5	RO	0		
4	RO	1	D. I	
3	RO	0	Reserved	
2	RO	1		
1	RO	0		
0	RO	0		

BYTE 18 (DPCD Address 00101h: Lane Count Set)

Bit	Type	Power-up Condition	Comment
7	RO	0	LANE_COUNT_SET
6	RO	0	Main-Link Lane Count = Value.
5	RO	0	Bit<4:0>LANE_COUNT_SET
4	RO	0	Three values are supported. All other values are RESERVED.
3	RO	0	Note: Because the upstream device is required to set this value within the MAX_LINK_RATE register (DPCD Address 00001h), there is no power-on
2	RO	1	reset default value for this field. It is suggested to program this field to 1h.
1	RO	0	(See the Note within the description for the LINK_BW_SET register (DPCD Address 00100h.)
0	RO	0	1h = 1 lane (Lane 0 only) 2h = 2 lanes (Lanes 0 and 1 only) 4h = 4 lanes A Source device may choose any lane count as long as it does not exceed the capability of the DPRX. For DPCD Ver.1.0: Bits <7:5> = RESERVED. Read all 0's. For DPCD Ver.1.1: Bits <6:5> = RESERVED. Read all 0's. Bit 7 = ENHANCED_FRAME_EN 0 = Enhanced Framing symbol sequence is not enabled. 1 = Enhanced Framing symbol sequence for BS and SR is enabled. Applicable to SST-only mode. A DPTX must set this bit to 1 when the DPRX has the ENHANCED_FRAME_CAP bit in the MAX_LANE_COUNT register (DPCD Address 00002h, bit 7) set to 1.

BYTE 19 - 30 (Reserved)





BYTE 31 (D	SYTE 31 (DPCD Address 00600h: SET DP Power)			
Bit	Type	Power-up Condition	Comment	
7	RO	0	SET_POWER_STATE	
6	RO	0	Bit 2:0 -001 = Set local Sink device and all downstream Sink devices to D0 (normal	
5	RO	0	operation mode).	
4	RO	0	010 = Set local Sink device and all downstream Sink devices to D3 (power	
3	RO	0	down mode). 101 = Set Main-Link for local Sink device and all downstream Sink devices	
2	RO	0	to D3 (power-down mode), keep AUX block fully powered, ready to reply	
1	RO	0	within a Response Timeout period of 300us.	
0	RO	1	All other values are RESERVED.	





Maximum Ratings

(Above which useful life may be impaired. For user guidelines, not tested.)

Storage Temperature
Junction Temperature
Supply Voltage to Ground Potential –0.5V to VDD+0.3V
Voltage Input to High Speed Differential Pins –0.5V to VDD
Voltage Input to Low Speed Pins (SCL, SDA) -0.5 V to $+3.6$ V
Voltage Input to Low Speed Pins (AUXP/N) -0.5 V to $+3.6$ V
ESD, HBM
ESD, CDM1KV

Note:

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Thermal Information

Symbol	Parameter	32-Pin X2QFN Package	Units
Theta JA	Junction to Ambient Thermal Resistance	49.7	°C/W

Recommended Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Units
V_{DD}	Supply Voltage	1.71	1.8	1.89	V
V _{DD_Noise}	Power Supply Noise Up to 50MHz			50	mVpp
V _{RX_CM}	Input Source Common-Mode Noise			150	mVpp
Cac_coupling	System AC Coupling Capacitance			265	nF
T_{A}	Ambient Temperature	-40(1)		+85	°C

Note:

Power Consumption

Symbol	Parameter	Min.	Тур.	Max.	Units
I _{ON_4DP}	4-lane DP2.1		160	220	mA
I_{D3}	Display Port D3 power down mode		1	1.6	mA

AC/DC Characteristics

 $VDD = 1.8 \pm 5\%, T_A = -40$ °C to 85°C

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units	
Receiver (RX)	Receiver (RX) (100Ω Differential) Electrical Specification						
R _{RX-DIFF-DC}	DC Differential Input Impedance		72		120	Ω	

^{1.} The minimum temperature -40 $^{\rm o}$ C guaranteed by design





Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
R _{RX-SINGLE-} DC	DC single ended input impedance to guarantee RxDet	Measured with respect to GND over a voltage of 500mV max	18		30	Ω
Z _{RX-HIZ-DC-} PD	DC input CM input impedance for V>0 during reset or power down	(Vcm = 0 to 500mV)	25			kΩ
Cac_coupling	AC coupling capacitance		75		265	nF
V _{RX-CM-AC-P}	Rx common mode peak voltage	AC up to 5GHz			150	mVpeak
V _{RX-CM-DC-} Active-Idle- Delta-P	Common mode peak voltage AvgU0 (VTX-D+ + VTX-D-)/2 -AvgU1 (VTX-D+ + VTX-D-)/2				200	mVpeak
Transmitter (ΓX) Electrical Specification					
V _{TX-DIFF-PP}	Output differential p-p voltage Swing	Differential Swing V _{TX-D+} - V _{TX-D-}		1		Vppd
R _{TX-DIFF-DC}	DC Differential TX Impedance		72		120	Ω
V _{TX-RCV-DET}	The amount of Voltage change allowed during RxDet	Type-C Tx Spec +/-60mA			600	mV
Cac-coupling	AC coupling capacitance		75		265	nF
R _{TX-DC-CM}	Common mode DC output Impedance		18		30	Ω
I _{TX-SHORT}	Transmitter short circuit current limit				60	mA
V _{TX-C}	Common-Mode Voltage	V _{TX-D+} + V _{TX-D-} /2	VDD-1V		VDD	V
V _{TX-DC-CM}	Instantaneous allowed DC common mode voltage at the connector side of the AC coupling capacitors	V _{TX-D+} + V _{TX-D-} /2	0		VDD	V
V _{TX-CM-AC-} PP-Active	Active mode TX AC common mode voltage	$V_{TX-D+} + V_{TX-D-}$ for both time and amplitude			100	mVpp
V _{TX-Idle-Diff-} AC-pp	Idle mode AC common mode delta voltage V _{TX-D+} -V _{TX-D-}	Between D+ and D- in idle mode. Use the HPF to remove DC components. =1/LPF.			10	mVppd
V _{TX-Idle-Diff-} DC	Idle mode DC common mode delta voltage V _{TX-D+} -V _{TX-D-}	Between D+ and D- in idle mode. Use the LPF to remove AC components. =1/HPF.			10	mV
Channel Perfo	ormance					
T_{pd}	Latency	From input to output		60	150	ps





Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units		
		EQ<2:0> = 000		6				
		EQ<2:0> = 001		8.5				
		EQ<2:0> = 010		10.8				
	Peaking gain (Compensation	EQ<2:0> = 011		12.7		4D		
G_{P_USB}	at 10GHz, relative to 100MHz,	EQ<2:0> = 100		14.2		dB		
	100mVp-p sine wave input, FG=0)	EQ<2:0> = 101		15.2				
		EQ<2:0> = 110		15.8				
		EQ<2:0> = 111		16.2				
		Variation around typical	-2		+2	dB		
$G_{ m F}$		FG<1:0> = 00		-4				
		FG<1:0> = 01		-2		dB		
	Flat gain (100MHz, EQ<2:0>=000)	FG<1:0> = 10		0		αБ		
		FG<1:0> = 11		+2				
		Variation around typical	-2		+2	dB		
V _{sw_100M}	Output linear swing (at 100MHz) EQ<2:0> = 000		910		mVppd			
V _{sw_10G}	Output linear swing (at 10GHz)	EQ<2:0> = 000		1000		mVppd		
DDNEXT	Differential near-end crosstalk	100MHz to 10GHz, Figure 6		-30		dB		
DDFEXT (2)	Differential far-end crosstalk	100MHz to 10GHz, Figure 7		-30		dB		
		100MHz to 10GHz, EQ<2:0> = 000, FG<1:0> = 10, Figure 8		0.6				
V _{NOISE_IN}	Input-referred noise	100MHz to 10GHz, EQ<2:0> = 111, FG<1:0> = 10, Figure 8		0.3		mV _{RMS}		
		100MHz to 10GHz, EQ<2:0> = 000, FG<1:0> = 10, Figure 8		0.3				
V _{NOISE_OUT}	Output-referred noise	100MHz to 10GHz, EQ<2:0> = 111, FG<1:0> = 10, Figure 8		0.5		mV _{RMS}		
S11DM	Input differential mode return loss	10MHz to 10GHz differential mode		-11.5	-8.1	dB		
S11CM	Input common mode return loss	1GHz to 10GHz common mode		-10	-5	dB		
S22DM	Output differential mode return loss	10MHz to 10GHz differential mode		-12.5	-8.1	dB		
S22CM	Output common mode return loss	1GHz to 10GHz common mode		-8	-4	dB		
DisplayPort E	Electrical Specification	1			1			
V _{TX-C}	Common-Mode Voltage	$ V_{TX-D+} + V_{TX-D-} /2$	VDD-1V		VDD	V		
V _{TX-AC-CM} HBR_RBR	TX AC common mode voltage for HRB and RBR	Measured using an 8b/10b pattern			20	mVrms		
V _{TX-AC-CM} HBR2	TX AC common mode voltage for HBR2	with 50% transition density			30	mVrms		





Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V _{TX-DIFFp-p-} Level0	Differential peak-to-peak output voltage swing Level 0	Tested with Pre-emphasis at	0.34	0.4	0.46	V
V _{TX-DIFFp-p-} Level1	Differential peak-to-peak output voltage swing Level 1	Level $0 = 0$ dB Level $1 = 3.5$ dB	0.51	0.6	0.68	V
V _{TX-DIFFp-p-} Level2	Differential peak-to-peak output voltage swing Level 2	Level $2 = 6.0$ dB	0.69	0.8	0.92	V
	UHBR20(20Gbps) TP2				0.45	UI
	UHBR13(13.5Gbps) TP2				0.45	UI
	UHBR10(10Gbps) TP2				0.38	UI
Tj TX Total Iitter	HBR3 (8.1Gbps)	Measured at Transmit output. Pre- channel loss from 2.5dB to 13dB			0.27	UI
)icter	HBR2 (5.4Gbps)	enamer ross from 2.3db to 13db			0.27	UI
	HBR (2.7Gbps)				0.294	UI
	RBR (1.62Gbps)				0.18	UI
AUX Listener	Electrical Specification					
C _{in}	Input capacitance at AUXP or AUXN				10	pF
VT(AUX_lis-tener)	Threshold of the AUX listener	VCC = 1.8V	100		220	mVPPd

Note:

^{1.} Measured using a vector-network analyzer (VNA) with -30dBm power level applied to the adjacent input. The VNA detects the signal at the output of the victim channel. All other inputs and outputs are terminated with 50Ω .

^{2.} Subtract the channel gain from the total gain to derive the actual crosstalk





Control Pin Specifications

 $VDD = 1.8 \pm 5\%, T_A = -40^{\circ}C \text{ to } 85^{\circ}C$

Symbol	Parameter	Min.	Тур.	Max.	Units
4-level Cont	rol Pins				
V_{IH}	DC input logic "High"	0.92*VDD	VDD	VDD+0.3	V
$V_{ m IF}$	DC input logic "Float"F	0.59*VDD	0.67*VDD	0.75*VDD	V
V_{IR}	DC input logic "With Rext to GND" R	0.25*VDD	0.33*VDD	0.41*VDD	V
$ m V_{IL}$	DC input logic "Low"	GND-0.3	GND	0.08*VDD	V
$ m I_{IH}$	Input high current			50	uA
$ m I_{IL}$	Input Low current	-75			uA
Rext	External resistance connects to GND (+/-5%)	64.6	68	71.4	$k\Omega$
IN_HPD In	put Pins				
V_{IH}	DC input logic high	1.7		3.6	V
V_{IL}	DC input logic low	GND-0.3		0.8	V
Rin	Termination to GND	100			kΩ





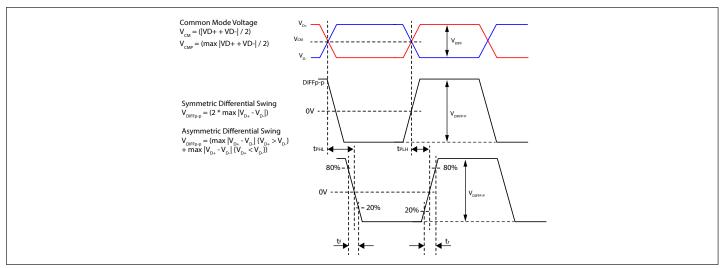


Figure 4. Definition of Peak-to-peak Differential Voltage

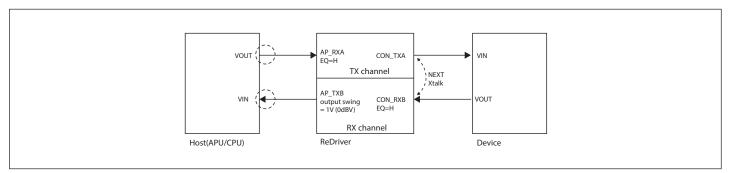


Figure 5. NEXT Crosstalk Definition

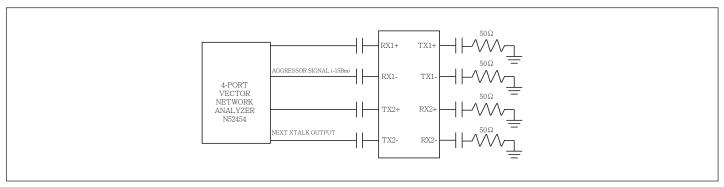


Figure 6. NEXT Channel-isolation Test Configuration





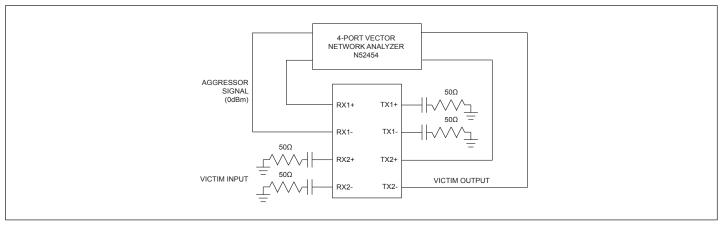


Figure 7. FEXT Channel-isolation Test Configuration

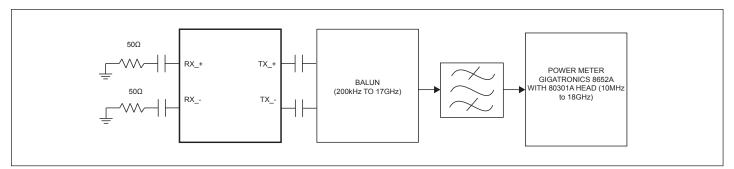


Figure 8. Noise Test Configuration

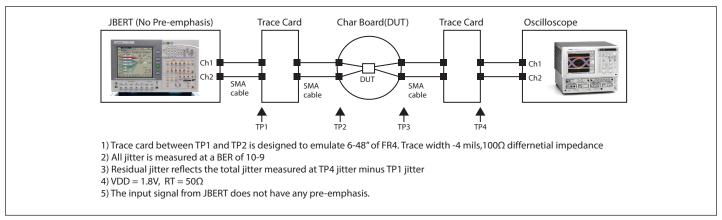


Figure 9. Channel Measurement Setup





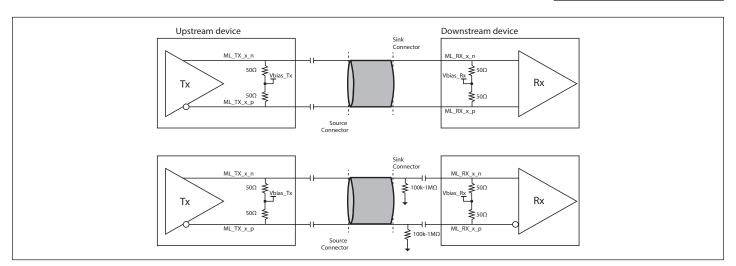


Figure 10. High-speed Channel Test Circuit

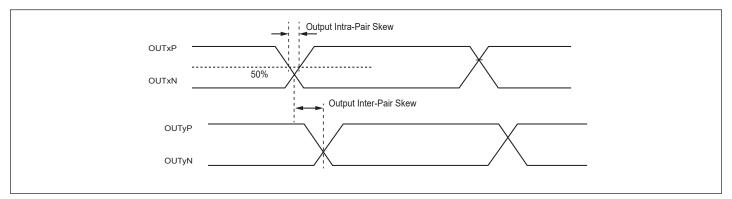


Figure 11. Intra and Inter-pair Differential Skew Definition





12C Electrical Specification and Timing

Characteristics of the SDA and SCL I/O Stages

Symbol	Parameter	Conditions	Min.	Max.	Units
$V_{\rm IL}$	LOW-level input voltage		-0.5	0.4	V
V_{IH}	HIGH-level input voltage		1.4		V
V _{OL1}	LOW-level output voltage 1	Open-drain or open-collector at 3mA sink current; V _{DD} >2V	0	0.4	V
I _{OL}	LOW-level output current	$V_{OL} = 0.4V$	20		mA
t _{of}	Output fall time from V_{IHmin} to V_{ILmax}		12	120	ns
t_{SP}	Pulse width of spikes that must be suppressed by the input filter		0	50	ns
Ii	Input current each I/O pin	0.1V _{DD} <v<sub>I < 0.9V_{DDmax}</v<sub>	-10	+10	uA
Ci	Capacitance for each I/O pin			10	pF

Characteristics of the SDA and SCL Bus Lines the Devices

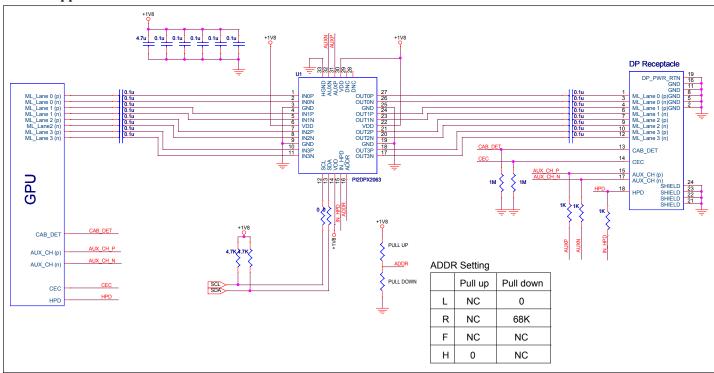
Symbol	Parameter	Conditions	Min.	Max.	Units
f_{SCL}	SCL clock frequency		10	1000	kHz
t _{HD;STA}	Hold time (repeated) START condition				us
t_{LOW}	LOW period of the SCL clock		0.5		us
t _{HIGH}	HIGH period of the SCL clock		0.26		us
t _{SU;STA}	Set-up time for a repeated START condition		0.26		us
t _{SU;DAT}	Data set-up time		50		ns
t _r	Rise time of both SDA and SCL signals			120	ns
t _f	Fall time of both SDA and SCL signals		12	120	ns
t _{SU;STO}	Set-up time for STOP condition		0.26		us
$t_{ m BUF}$	Bus free time between a STOP and START condition		0.5		us
C _b	Capacitive load for each bus line			550	pF
t _{VD;DAT}	Data valid time			0.45	us
t _{VD;ACK}	Data valid acknowledge time			0.45	us
V_{nL}	Noise margin at the LOW level	For each connected device (including hysteresis)	$0.1 \mathrm{V}_\mathrm{DD}$		V
V_{nH}	Noise margin at the HIGH level	For each connected device (including hysteresis)	$0.2 \mathrm{V}_\mathrm{DD}$		V



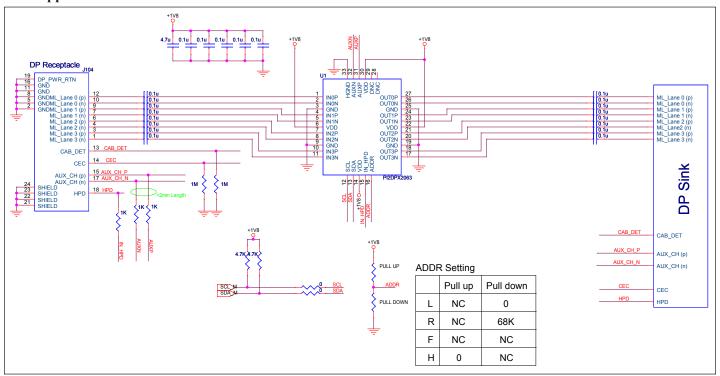


Application Schematics

Source Application Circuit



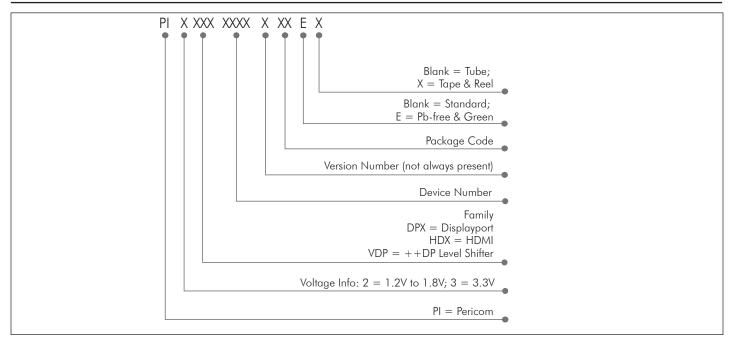
Sink Application Circuit







Device Naming Information



Part Marking

 $\begin{array}{c} \text{PI2DPX2} \\ \text{063FLAE} \\ \text{ZYWX} \overline{\text{X}} \end{array}$

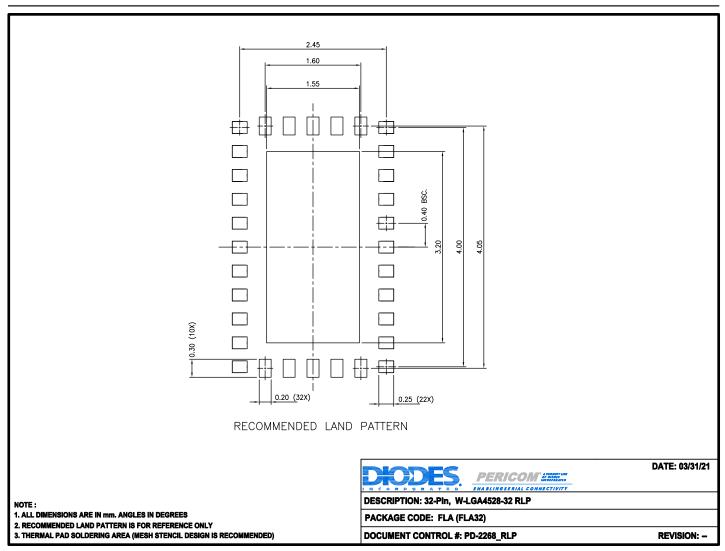
Z: Die Rev Y: Year W: Week

1st X: Assembly Code 2nd X: Fab Code





Recommended Land Pattern

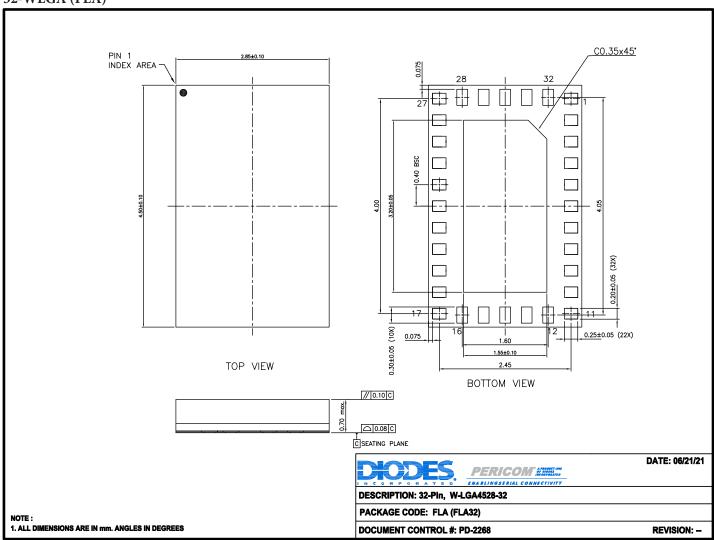






Packaging Mechanical

32-WLGA (FLA)



22-0634

For latest package info.

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Tape & Reel Materials and Design

Carrier Tape

The pocketed carrier tape is made of conductive polystyrene plus carbon material (or equivalent). The surface resistivity is 106Ω /sq. maximum. Pocket tapes are designed so that the component remains in position for automatic handling after cover tape is removed. Each pocket has a hole in the center for automated sensing if the pocket is occupied or not, thus facilitating device removal. Sprocket holes along the edge of the center tape enable direct feeding into automated board assembly equipment. See figures C and D for carrier tape dimensions.

Cover Tape

Cover tape is made of anti-static transparent polyester film. The surface resistivity is $107\Omega/\text{sq}$. Minimum to $1011\Omega/\text{sq}$. maximum. The cover tape is heat-sealed to the edges of the carrier tape to encase the devices in the pockets. The force to peel back the cover tape from the carrier tape shall be a MEAN value of 20gm to 80gm (2N to 0.8N).

Reel

The device loading orientation is in compliance with EIA-481, current version (Figure B). The loaded carrier tape is wound onto either a 13-inch reel (Figure D) or 7-inch reel. The reel is made of Antistatic High-Impact Polystyrene. The surface resistivity $107\Omega/\text{sq}$, minimum to $1011\Omega/\text{sq}$, maximum.

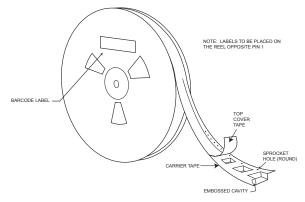


Figure A. Tape & Reel Label Information

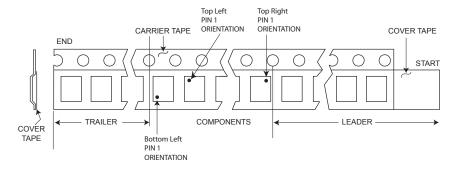


Figure B. Tape Leader and Trailer Pin 1 Orientations





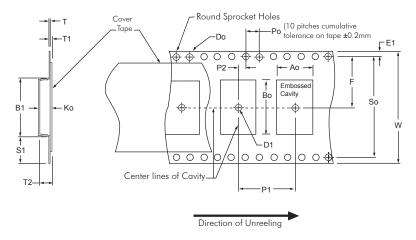


Figure C. Standard Embossed Carrier Tape Dimensions

Tape & Reel Dimensions

Constant Dimensions

Constant D	michigions									
TAPE SIZE	D_0	D ₁ (Min)	E ₁	P ₀	P ₂	R (2)	S ₁ (Min)	T (Max)	T ₁ (Max)	
8mm		1.0			201005	25				
12mm					2.0 ± 0.05		0.6			
16mm	15.0100	1.5	1.75 + 0.1	40+01		30	0.6	0.6	0.1	
24mm	1.5 +0.1-0.0		1.75 ± 0.1	4.0 ± 0.1	2.0 ± 0.1	2.0 ± 0.1		0.6	0.1	
32mm		2.0				50	N/A ⁽³⁾			
44mm			2.0			2.0 ± 0.15	50	IN/A (5)		

Variable Dimensions

variable Di								
TAPE SIZE	P ₁	B ₁ (Max)	E ₂ (Min)	F	So	T ₂ (Max)	W (Max)	A ₀ , B ₀ &K ₀
8mm	Specific per package type. Refer to FR-0221 (Tape and Reel Packing	4.35	6.25	3.5 ± 0.05		2.5	8.3	
12mm		8.2	10.25	5.5 ± 0.05	N/A ⁽⁴⁾	6.5	12.3	
16mm	Information) or visit	12.1	14.25	7.5 ± 0.1	N/A (*)	8.0	16.3	C N. 1
24mm	www.diodes.com/assets/	20.1	22.25	11.5 ± 0.1		12.0	24.3	See Note 1
32mm	MediaList-Attachments/ Diodes-Tape-Reel-Tube.	23.0	N/A	14.2 ± 0.1	28.4 ± 0.1	12.0	32.3	
44mm	pdf	35.0	N/A	20.2 ± 0.15	40.4 ± 0.1	16.0	44.3	

NOTES:

- 1. A₀, B₀, and K₀ are determined by component size. The cavity must restrict lateral movement of component to 0.5mm maximum for 8mm and 12mm wide tape and to 1.0mm maximum for 16mm, 24mm, 32mm, and 44mm wide carrier. The maximum component rotation within the cavity must be limited to 200 maximum for 8 and 12 mm carrier tapes and 100 maximum for 16mm through 44mm.
- 2. Tape and components will pass around reel with radius "R" without damage.
- 3. S_1 does not apply to carrier width ≥ 32 mm because carrier has sprocket holes on both sides of carrier where $D_0 \geq S_1$.
- 4. S_0 does not exist for carrier \leq 32mm because carrier does not have sprocket hole on both side of carrier.





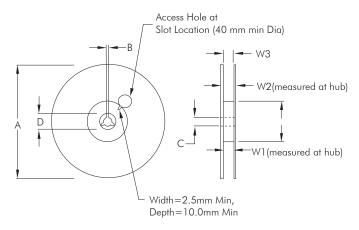


Figure D. Reel Dimensions

Reel Dimensions By Tape Size

Rect Difficultions by Tupe Oize								
TAPE SIZE	A	N (Min) (1)	W_1	W ₂ (Max)	W ₃	B (Min)	С	D (Min)
8mm	178 ± 2.0mm or 330 ± 2.0mm	60 ± 2.0mm or 100 ± 2.0mm	8.4 +1.5/-0.0mm	14.4mm	Shall Accommodate Tape Width Without Interference	1.5mm	13.0 +0.5/-0.2 mm	20.2mm
12mm			12.4 +2.0/-0.0mm	18.4mm				
16mm	330 ± 2.0mm	100 ± 2.0mm	16.4 +2.0/-0.0mm	22.4mm				
24mm			24.4 +2.0/-0.0mm	30.4mm				
32mm			32.4 +2.0/-0.0mm	38.4mm				
44mm			44.4 +2.0/-0.0mm	50.4mm				

Note:

^{1.} If reel diameter A=178 \pm 2.0mm, then the corresponding hub diameter (N(min) will by 60 \pm 2.0mm. If reel diameter A=330 \pm 2.0mm, then the corresponding hub diameter (N(min)) will by 100 \pm 2.0mm.





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